This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

IRHNJ57230SE (2N7486U3)
200V, N-Channel, TID Hardened MOSFET in a SMD-0.5 package

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS
trr [Reverse Recovery Time], change test condition V_{DD} from ≤ 25V to V_{DD} ≤ 50V

RADIATION CHARACTERISTICS CHANGE:
Table 1 Electrical Characteristics @ T_j = 25°C, Post Total Dose Irradiation
loss [Zero Gate Voltage Drain Current], change test condition V_{DS} from 200V to 160V
V_{DS} [Diode Forward Voltage], change maximum limit from 1.3V to 1.2V
Radiation Level, change/correct TID from 1000kRads (Si) to 100kRads (Si)

Reference Datasheet PD-93836